**Product data sheet** 

## 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN0606-3 (SOT8001) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection up to 1.8 kV HBM
- Leadless ultra small and ultra thin SMD plastic package: 0.62 × 0.62 × 0.37 mm

## 3. Applications

- Relay driver
- High-speed line driver
- · High-side load switch
- · Switching circuits

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-20	V
V <sub>GS</sub>	gate-source voltage			-8	-	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-	-0.8	Α
Static characte	Static characteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -0.6 \text{ A}; T_j = 25 \text{ °C}$		-	550	640	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.



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# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		D
2	S	source		
3	D	drain	Transparent top view DFN0606-3 (SOT8001)	G S S 017aaa259

# 6. Ordering information

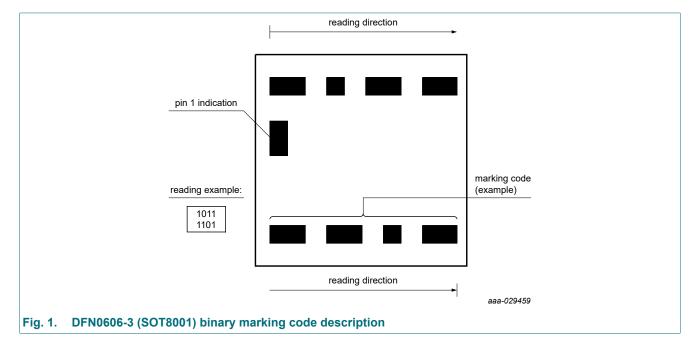
**Table 3. Ordering information** 

Type number Package							
	Name	Description	Version				
PMH550UPE	DFN0606-3	plastic, leadless ultra small package; 3 terminals; body 0.62 x 0.62 x 0.37 mm	SOT8001				

# 7. Marking

Table 4. Marking codes

Type number	Marking code
PMH550UPE	0001 1000



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## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-20	V
$V_{GS}$	gate-source voltage			-8	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-0.8	Α
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	-0.5	А
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-2	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	0.36	W
			[1]	-	0.66	W
		T <sub>sp</sub> = 25 °C		-	2.23	W
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drai	n diode					
Is	source current	T <sub>amb</sub> = 25 °C	[1]	-	-0.6	Α

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

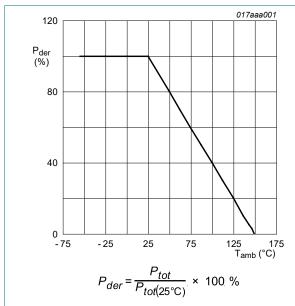


Fig. 2. Normalized total power dissipation as a function of ambient temperature

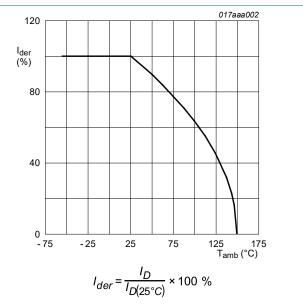


Fig. 3. Normalized continuous drain current as a function of ambient temperature

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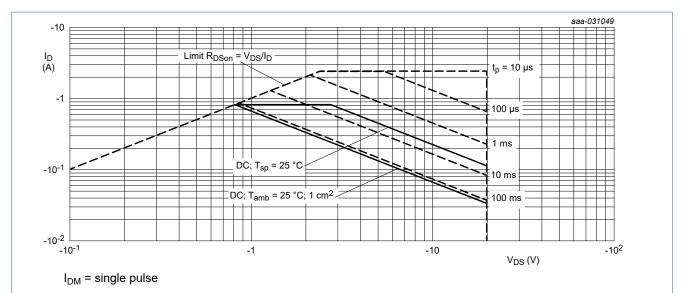


Fig. 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

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### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from	in free air	[1]	-	287	344	K/W
junction to ambient		[2]	-	158	190	K/W	
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	47	56	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.

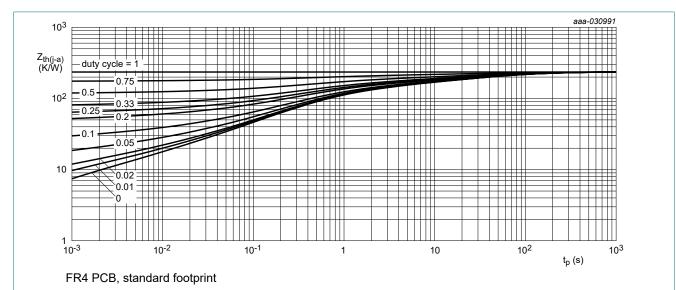


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

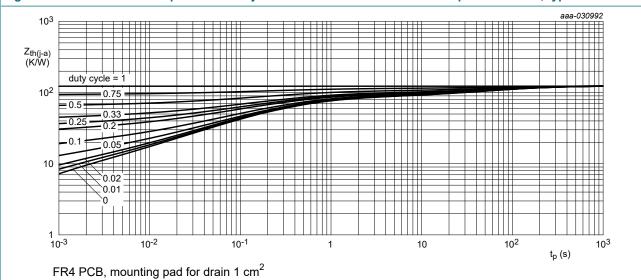


Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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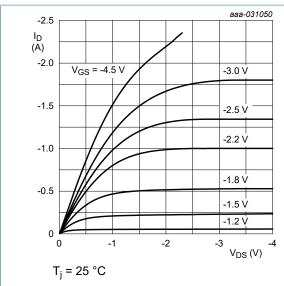
# 10. Characteristics

#### **Table 7. Characteristics**

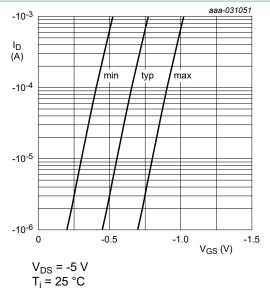
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-20	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 °C$	-0.45	-0.7	-0.95	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = -20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μA
		V <sub>DS</sub> = -20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C	-	-	-20	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = -8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-5	μA
		V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	5	μΑ
		$V_{GS} = -4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	-1	μΑ
		V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μΑ
		V <sub>GS</sub> = -2.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-100	nA
		$V_{GS} = 2.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	100	nA
R <sub>DSon</sub>		$V_{GS} = -4.5 \text{ V}; I_D = -0.6 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	550	640	mΩ
resista	resistance	$V_{GS} = -4.5 \text{ V}; I_D = -0.6 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	850	990	mΩ
		$V_{GS} = -2.5 \text{ V}; I_D = -0.3 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	788	930	mΩ
		$V_{GS} = -1.8 \text{ V}; I_D = -0.08 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	1.17	1.9	Ω
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = -10 V; $I_{D}$ = -0.6 A; $T_{j}$ = 25 °C	-	1.1	-	S
R <sub>G</sub>	gate resistance	f = 1 MHz	-	19.2	-	Ω
Dynamic ch	naracteristics		,		'	
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = -10 V; $I_{D}$ = -0.6 A; $V_{GS}$ = -4.5 V;	-	0.6	0.9	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	0.1	-	nC
$Q_{GD}$	gate-drain charge		-	0.16	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = -10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	54.8	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	11.2	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	7.7	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = -10 \text{ V}; I_D = -0.6 \text{ A}; V_{GS} = -4.5 \text{ V};$	-	2	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	2	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	5	-	ns
t <sub>f</sub>	fall time		-	3	-	ns
Source-dra	in diode		'		·	
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = -0.6 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-0.7	-1.2	V

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Output characteristics: drain current as a Fig. 7. function of drain-source voltage; typical values



 $T_i = 25 \,^{\circ}\text{C}$ 

Sub-threshold drain current as a function of Fig. 8. gate-source voltage

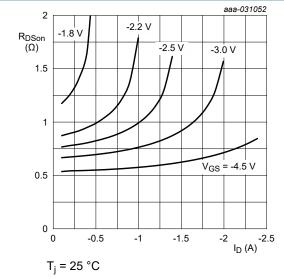


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

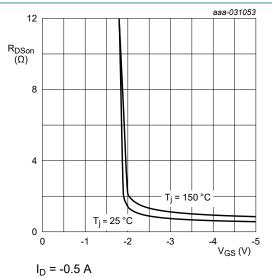


Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

#### 20 V, P-channel Trench MOSFET

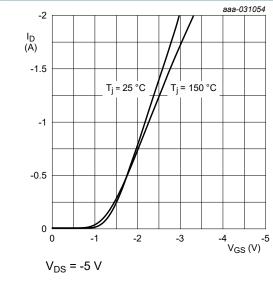


Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

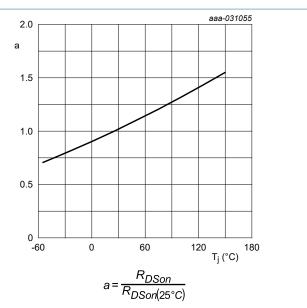


Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values

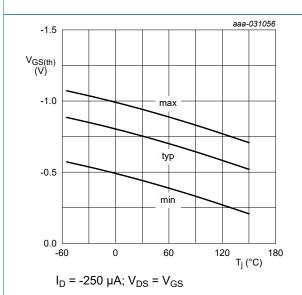


Fig. 13. Gate-source threshold voltage as a function of junction temperature

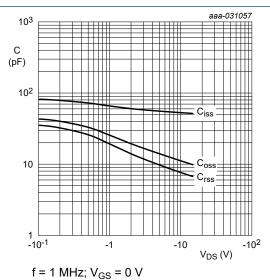


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

### 20 V, P-channel Trench MOSFET

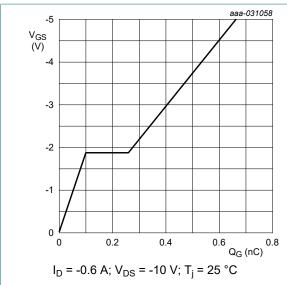


Fig. 15. Gate-source voltage as a function of gate charge; typical values

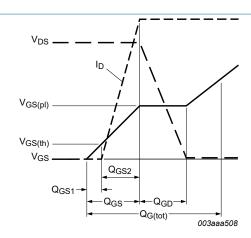


Fig. 16. Gate charge waveform definitions

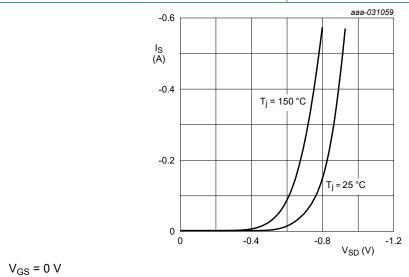
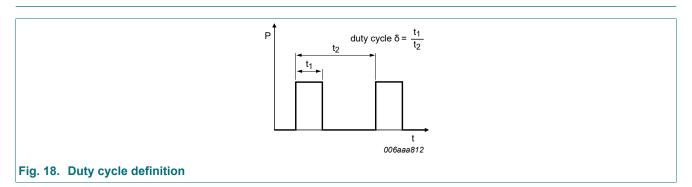


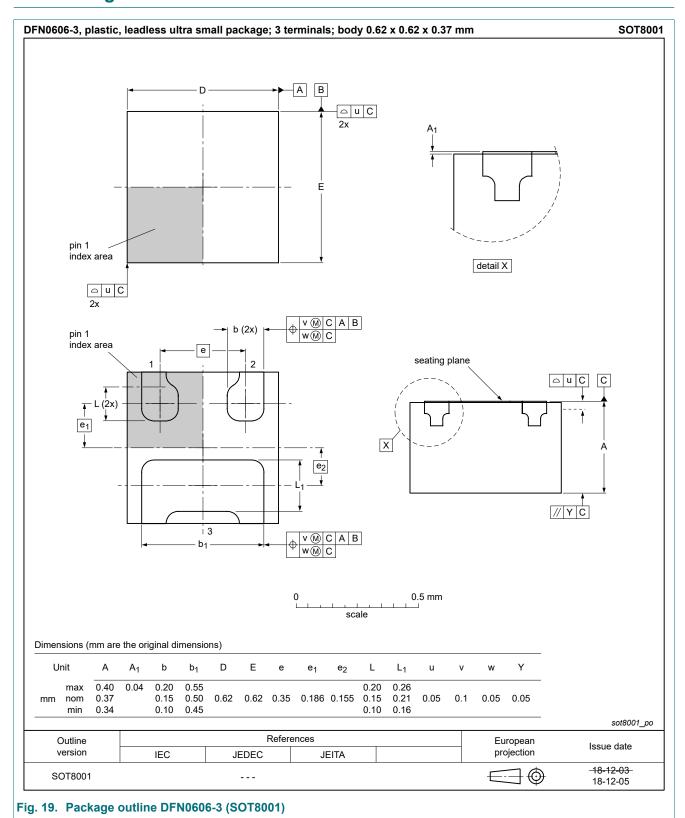
Fig. 17. Source current as a function of source-drain voltage; typical values

### 11. Test information



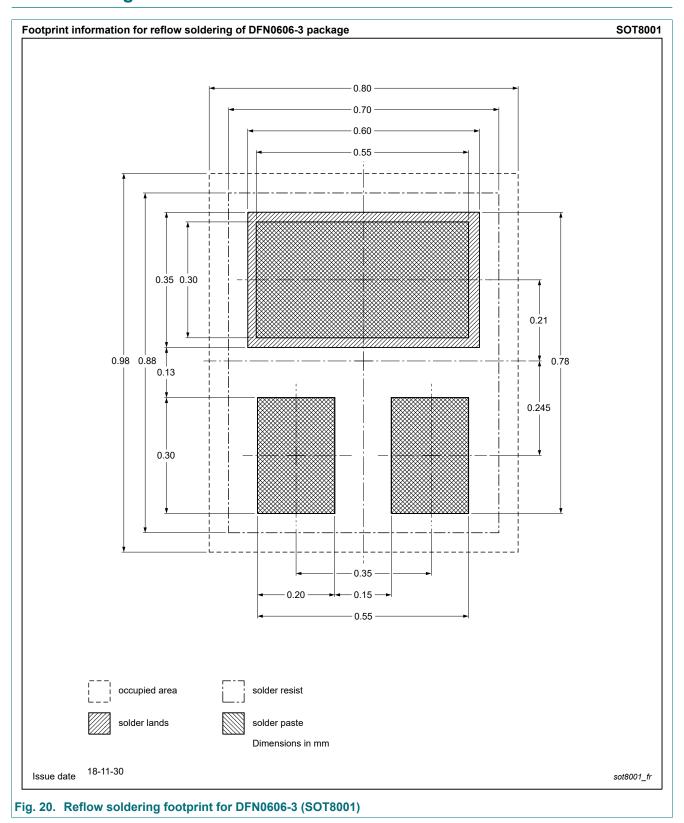
20 V, P-channel Trench MOSFET

# 12. Package outline



20 V, P-channel Trench MOSFET

# 13. Soldering



20 V, P-channel Trench MOSFET

# 14. Revision history

#### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMH550UPE v.1	20200408	Product data sheet	-	-

### 20 V, P-channel Trench MOSFET

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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